

7. (Amended) The multilayer ceramic capacitor as set forth in claim 1, wherein a thickness of at least one of said dielectric layers is less than $3\mu\text{m}$.

8. (Amended) The multilayer ceramic capacitor as set forth in claim 2, wherein a thickness of at least one of said dielectric layers is less than $3\mu\text{m}$.

9. (Amended) The multilayer ceramic capacitor as set forth in claim 3, wherein a thickness of at least one of said dielectric layers is less than $3\mu\text{m}$.

4.10. (Amended) The multilayer ceramic capacitor as set forth in claim 1, wherein at least one of said dielectric layers comprises at least said dielectric particles and a grain boundary phase, and an area ratio of said grain boundary phase in a section of said dielectric layer is 2% or less.

11. (Amended) The multilayer ceramic capacitor as set forth in claim 2, wherein at least one of said dielectric layers comprises at least said dielectric particles and a grain boundary phase, and an area ratio of said grain boundary phase in a section of said dielectric layer is 2% or less.

6.14. (Amended) The multilayer ceramic capacitor as set forth in claim 1, wherein at least one of said dielectric layers is comprised of dielectric particles, a grain boundary and grain boundary phase, a segregation phase exists in said grain boundary phase, and said segregation phase contains at least two kinds of elements selected from the group consisting of Mn, Y, Si, Ca, V and W.

15. (Amended) The multilayer ceramic capacitor as set forth in claim 2, wherein at least one of said dielectric layers is comprised of dielectric particles, a grain boundary and grain boundary phase, a segregation phase exists in said grain boundary phase, and said segregation phase contains at least two kinds of elements selected from the group consisting of Mn, Y, Si, Ca, V and W.